Gilles Patriarche

List of Publications by Year in Descending Order

593 papers	12,685 citations	55 h-index	87 g-index
657 ext. papers	14,136 ext. citations	4.1 avg, IF	6.31 L-index

#	Paper	IF	Citations
593	Up to 300 K lasing with GeSn-On-Insulator microdisk resonators.. *Optics Express*, **2022**, 30, 3954-3961	3.3	2
592	Influence of Sapphire Substrate Orientation on the van der Waals Epitaxy of III-Nitrides on 2D Hexagonal Boron Nitride: Implication for Optoelectronic Devices. *ACS Applied Nano Materials*, **2022**, 5, 791-800	5.6	0
591	Nanoindentation investigation of solid-solution strengthening in III-V semiconductor alloys. *International Journal of Materials Research*, **2022**, 96, 1237-1241	0.5	1
590	Electroluminescence from nanocrystals above 2 μm. *Nature Photonics*, **2022**, 16, 38-44	33.9	6
589	Photo-Activated Phosphorescence of Ultrafine ZnS:Mn Quantum Dots: On the Lattice Strain Contribution. *Journal of Physical Chemistry C*, **2022**, 126, 1531-1541	3.8	
588	Indentation behaviour of (011) thin films of III-V semiconductors: polarity effect differences between GaAs and InP. *International Journal of Materials Research*, **2022**, 97, 1230-1234	0.5	
587	In-Situ Transmission Electron Microscopy Observation of Germanium Growth on Freestanding Graphene: Unfolding Mechanism of 3D Crystal Growth During Van der Waals Epitaxy. *Small*, **2021**, e2101890	11	
586	GeSnOI mid-infrared laser technology. *Light: Science and Applications*, **2021**, 10, 232	16.7	5
585	Porous nanoparticles with engineered shells release their drug cargo in cancer cells. *International Journal of Pharmaceutics*, **2021**, 610, 121230	6.5	2
584	Development of Micron Sized Photonic Devices Based on Deep GaN Etching. *Photonics*, **2021**, 8, 68	2.2	1
583	Temperature dependence of optical properties of InAs/InP quantum rod-nanowires grown on Si substrate. *Journal of Luminescence*, **2021**, 231, 117814	3.8	0
582	Degradation Mechanism of Porous Metal-Organic Frameworks by In Situ Atomic Force Microscopy. *Nanomaterials*, **2021**, 11,	5.4	9
581	Band-Gap Landscape Engineering in Large-Scale 2D Semiconductor van der Waals Heterostructures. *ACS Nano*, **2021**, 15, 7279-7289	16.7	8
580	Fabrication and characterization of ZnO:Sb/n-ZnO homojunctions. *Applied Physics A: Materials Science and Processing*, **2021**, 127, 1	2.6	
579	Correlating Structure and Detection Properties in HgTe Nanocrystal Films. *Nano Letters*, **2021**, 21, 4145-4151	11.1	12
578	Monolithic Free-Standing Large-Area Vertical III-N Light-Emitting Diode Arrays by One-Step h-BN-Based Thermomechanical Self-Lift-Off and Transfer. *ACS Applied Electronic Materials*, **2021**, 3, 2614-2621	4	3
577	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride: A key enabler of III-nitride flexible optoelectronics. *APL Materials*, **2021**, 9, 061101	5.7	2

576	Spray-Drying Polymer Encapsulation of CsPbBr3 Perovskite Nanocrystals with Enhanced Photostability for LED Downconverters. *ACS Applied Nano Materials*, **2021**, 4, 7502-7512	5.6	1
575	Experimental quantification of atomically-resolved HAADF-STEM images using EDX. *Ultramicroscopy*, **2021**, 220, 113152	3.1	1
574	Engineering a Robust Flat Band in III-V Semiconductor Heterostructures. *Nano Letters*, **2021**, 21, 680-685	11.5	3
573	Efficient Electrical Transport Through Oxide-Mediated InP-on-Si Hybrid Interfaces Bonded at 300 °C. *Physica Status Solidi (A) Applications and Materials Science*, **2021**, 218, 2000317	1.6	
572	Topological surface states in epitaxial (SnBi2Te4)n(Bi2Te3)m natural van der Waals superlattices. *Physical Review Materials*, **2021**, 5,	3.2	3
571	Metal–organic framework/graphene oxide composites for CO2 capture by microwave swing adsorption. *Journal of Materials Chemistry A*, **2021**, 9, 13135-13142	13	6
570	Development of a cryogenic indentation tool with in situ optical observation, application to the mechanical characterization of II–VI semiconductors. *Semiconductor Science and Technology*, **2021**, 36, 035015	1.8	0
569	Interdiffusion of Al and Ga in AlN/AlGaN superlattices grown by ammonia-assisted molecular beam epitaxy. *Superlattices and Microstructures*, **2021**, 150, 106801	2.8	2
568	Strain, magnetic anisotropy, and composition modulation in hybrid metal–oxide vertically assembled nanocomposites. *MRS Bulletin*, **2021**, 46, 136-141	3.2	2
567	Electronic band gap of van der Waals As2Te3 crystals. *Applied Physics Letters*, **2021**, 119, 043103	3.4	0
566	Selective target protein detection using a decorated nanopore into a microfluidic device. *Biosensors and Bioelectronics*, **2021**, 183, 113195	11.8	6
565	Dynamics of Droplet Consumption in Vapor–Liquid–Solid III–V Nanowire Growth. *Crystal Growth and Design*, **2021**, 21, 4647-4655	3.5	1
564	Single-Electron Tunneling PbS/InP Heterostructure Nanoplatelets for Synaptic Operations. *ACS Applied Materials & Interfaces*, **2021**, 13, 38450-38457	9.5	1
563	Monodispersed MOF-808 Nanocrystals Synthesized via a Scalable Room-Temperature Approach for Efficient Heterogeneous Peptide Bond Hydrolysis. *Chemistry of Materials*, **2021**, 33, 7057-7066	9.6	9
562	Relaxation mechanism of GaP grown on 001 Si substrates: influence of defects on the growth of AlGaP layers on GaP/Si templates. *Philosophical Magazine*, **2021**, 101, 2189-2199	1.6	
561	Highly linear polarized emission at telecom bands in InAs/InP quantum dot-nanowires by geometry tailoring. *Nanoscale*, **2021**, 13, 16952-16958	7.7	
560	Effect of sintering germanium epilayers on dislocation dynamics: From theory to experimental observation. *Acta Materialia*, **2020**, 200, 608-618	8.4	1
559	Why is it difficult to grow spontaneous ZnO nanowires using molecular beam epitaxy?. *Nanotechnology*, **2020**, 31, 385601	3.4	1

558	Crystal phase engineering of self-catalyzed GaAs nanowires using a RHEED diagram. *Nanoscale Advances*, **2020**, 2, 2127-2134	5.1	6
557	Measuring the surface bonding energy: A comparison between the classical double-cantilever beam experiment and its nanoscale analog. *AIP Advances*, **2020**, 10, 045006	1.5	0
556	Ultra-low-threshold continuous-wave and pulsed lasing in tensile-strained GeSn alloys. *Nature Photonics*, **2020**, 14, 375-382	33.9	81
555	Encapsulation of Microperoxidase-8 in MIL-101(Cr)-X Nanoparticles: Influence of Metal□Organic Framework Functionalization on Enzymatic Immobilization and Catalytic Activity. *ACS Applied Nano Materials*, **2020**, 3, 3233-3243	5.6	10
554	Phase Selection in Self-catalyzed GaAs Nanowires. *Nano Letters*, **2020**, 20, 1669-1675	11.5	49
553	Pushing Absorption of Perovskite Nanocrystals into the Infrared. *Nano Letters*, **2020**, 20, 3999-4006	11.5	11
552	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. *Physical Review Materials*, **2020**, 4,	3.2	14
551	Structural, vibrational, and magnetic properties of self-assembled CoPt nanoalloys embedded in SrTiO3. *Physical Review Materials*, **2020**, 4,	3.2	1
550	3.3 □m interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. *Semiconductor Science and Technology*, **2020**, 35, 125029	1.8	1
549	Efficient incorporation and protection of lansoprazole in cyclodextrin metal-organic frameworks. *International Journal of Pharmaceutics*, **2020**, 585, 119442	6.5	4
548	Single crystalline boron rich B(Al)N alloys grown by MOVPE. *Applied Physics Letters*, **2020**, 116, 042101	3.4	7
547	Engineering dislocations and nanovoids for high-efficiency III□V photovoltaic cells on silicon **2020**,		1
546	Density-controlled growth of vertical InP nanowires on Si(111) substrates. *Nanotechnology*, **2020**, 31, 354003	3.4	2
545	Gate length dependent transport properties of in-plane core-shell nanowires with raised contacts. *Nano Research*, **2020**, 13, 61-66	10	1
544	Nanoscale electrical analyses of axial-junction GaAsP nanowires for solar cell applications. *Nanotechnology*, **2020**, 31, 145708	3.4	9
543	Microstructure of GaAs thin films grown on glass using Ge seed layers fabricated by aluminium induced crystallization. *Thin Solid Films*, **2020**, 694, 137737	2.2	3
542	Control of the Mechanical Adhesion of III-V Materials Grown on Layered h-BN. *ACS Applied Materials & Interfaces*, **2020**, 12, 55460-55466	9.5	4
541	Reduced Lasing Thresholds in GeSn Microdisk Cavities with Defect Management of the Optically Active Region. *ACS Photonics*, **2020**, 7, 2713-2722	6.3	19

540	Highly Ordered Boron Nitride/Epigraphene Epitaxial Films on Silicon Carbide by Lateral Epitaxial Deposition. *ACS Nano*, **2020**, 14, 12962-12971	16.7	5
539	Stable and high yield growth of GaP and InGaAs nanowire arrays using In as a catalyst. *Nanoscale*, **2020**, 12, 18240-18248	7.7	4
538	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. *Scientific Reports*, **2020**, 10, 21709	4.9	6
537	Effects of nitrogen incorporation and thermal annealing on the optical and spin properties of GaPN dilute nitride alloys. *Journal of Alloys and Compounds*, **2020**, 814, 152233	5.7	3
536	Molecular-beam epitaxy of GaSb on 6°-offcut (0 0 1) Si using a GaAs nucleation layer. *Journal of Crystal Growth*, **2020**, 529, 125299	1.6	3
535	Uprooting defects to enable high-performance III-V optoelectronic devices on silicon. *Nature Communications*, **2019**, 10, 4322	17.4	27
534	Physical mechanisms involved in the formation and operation of memory devices based on a monolayer of gold nanoparticle-polythiophene hybrid materials. *Nanoscale Advances*, **2019**, 1, 2718-2726	5.1	3
533	Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride. *Advanced Materials Interfaces*, **2019**, 6, 1900207	4.6	9
532	GaAs (1 1 1) epilayers grown by MBE on Ge (1 1 1): Twin reduction and polarity. *Journal of Crystal Growth*, **2019**, 519, 84-90	1.6	8
531	Importance of point defect reactions for the atomic-scale roughness of III-V nanowire sidewalls. *Nanotechnology*, **2019**, 30, 324002	3.4	2
530	Evidence and control of unintentional As-rich shells in GaAs P nanowires. *Nanotechnology*, **2019**, 30, 294003	3.4	4
529	Controlled Dislocations Injection in N/P $Hg_{1-x}CdxTe$ Photodiodes by Indentations. *Journal of Electronic Materials*, **2019**, 48, 6108-6112	1.9	
528	Correlated optical and structural analyses of individual GaAsP/GaP core-shell nanowires. *Nanotechnology*, **2019**, 30, 304001	3.4	3
527	Trap-Free Heterostructure of PbS Nanoplatelets on InP(001) by Chemical Epitaxy. *ACS Nano*, **2019**, 13, 1961-1967	16.7	6
526	Selective area molecular beam epitaxy of InSb nanostructures on mismatched substrates. *Journal of Crystal Growth*, **2019**, 512, 6-10	1.6	8
525	Composition and Face Polarity Influences on Mechanical Properties of (111) $Cd_{1-y}ZnyTe$ Determined by Indentation. *Journal of Electronic Materials*, **2019**, 48, 6985-6990	1.9	1
524	Evidence for a narrow band gap phase in 1T? WS2 nanosheet. *Applied Physics Letters*, **2019**, 115, 032102	3.4	16
523	Voided Ge/Si Platform to Integrate III-V Materials on Si. *ECS Transactions*, **2019**, 93, 81-85	1	2

522	Phase separation and surface segregation in $CoAu_3$-$SrTiO_3$ thin films: Self-assembly of bilayered epitaxial nanocolumnar composites. *Physical Review Materials*, **2019**, 3,	3.2	3
521	A study of the strain distribution by scanning X-ray diffraction on GaP/Si for III-V monolithic integration on silicon. *Journal of Applied Crystallography*, **2019**, 52, 809-815	3.8	2
520	A porous Ge/Si interface layer for defect-free III-V multi-junction solar cells on silicon **2019**,		3
519	Heteroepitaxial growth of silicon on GaAs via low-temperature plasma-enhanced chemical vapor deposition **2019**,		2
518	Polarization- and diffraction-controlled second-harmonic generation from semiconductor metasurfaces. *Journal of the Optical Society of America B: Optical Physics*, **2019**, 36, E55	1.7	15
517	InAs quantum dot in a needlelike tapered InP nanowire: a telecom band single photon source monolithically grown on silicon. *Nanoscale*, **2019**, 11, 21847-21855	7.7	10
516	Wafer-scale MOVPE growth and characterization of highly ordered h-BN on patterned sapphire substrates. *Journal of Crystal Growth*, **2019**, 509, 40-43	1.6	9
515	InAs/GaSb thin layers directly grown on nominal (0 0 1)-Si substrate by MOVPE for the fabrication of InAs FINFET. *Journal of Crystal Growth*, **2019**, 510, 18-22	1.6	1
514	Development of reflective back contacts for high-efficiency ultrathin Cu(In,Ga)Se2 solar cells. *Thin Solid Films*, **2019**, 672, 1-6	2.2	14
513	MOVPE van der Waals epitaxial growth of AlGaN/AlGaN multiple quantum well structures with deep UV emission on large scale 2D h-BN buffered sapphire substrates. *Journal of Crystal Growth*, **2019**, 507, 352-356	1.6	5
512	Growth optimization and characterization of regular arrays of GaAs/AlGaAs core/shell nanowires for tandem solar cells on silicon. *Nanotechnology*, **2019**, 30, 084005	3.4	11
511	High structural and optical quality of III-V-on-Si 1.2 nm-thick oxide-bonded hybrid interface. *Microelectronic Engineering*, **2018**, 192, 25-29	2.5	1
510	Determination of the spin orbit coupling and crystal field splitting in wurtzite InP by polarization resolved photoluminescence. *Applied Physics Letters*, **2018**, 112, 071903	3.4	3
509	Measuring and Modeling the Growth Dynamics of Self-Catalyzed GaP Nanowire Arrays. *Nano Letters*, **2018**, 18, 701-708	11.5	35
508	Shear-driven phase transformation in silicon nanowires. *Nanotechnology*, **2018**, 29, 125601	3.4	21
507	Biomimetic ion channels formation by emulsion based on chemically modified cyclodextrin nanotubes. *Faraday Discussions*, **2018**, 210, 41-54	3.6	6
506	Versatile cyclodextrin nanotube synthesis with functional anchors for efficient ion channel formation: design, characterization and ion conductance. *Nanoscale*, **2018**, 10, 15303-15316	7.7	7
505	Impact of the sequence of precursor introduction on the growth and properties of atomic layer deposited Al-doped ZnO films. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2018**, 36, 041502	2.9	6

504	Quantum cascade lasers grown on silicon. *Scientific Reports*, **2018**, 8, 7206	4.9	41
503	Universal description of III-V/Si epitaxial growth processes. *Physical Review Materials*, **2018**, 2,	3.2	30
502	Chemical nature of the anion antisite in dilute phosphide GaAs1−xPx alloy grown at low temperature. *Physical Review Materials*, **2018**, 2,	3.2	1
501	Ultrathin Ni nanowires embedded in SrTiO3: Vertical epitaxy, strain relaxation mechanisms, and solid-state amorphization. *Physical Review Materials*, **2018**, 2,	3.2	13
500	Atomic scale analyses of {bb Z}-module defects in an NiZr alloy. *Acta Crystallographica Section A: Foundations and Advances*, **2018**, 74, 647-658	1.7	2
499	Determination of the polarity of the GaAs (001) rosette arms by convergent beam electron diffraction **2018**, 445-448		
498	Large angle twist-bonded compliant substrates for the epitaxy of lattice mismatched III-V semiconductors **2018**, 193-196		
497	Interface energy analysis of III-V islands on Si (001) in the Volmer-Weber growth mode. *Applied Physics Letters*, **2018**, 113, 191601	3.4	9
496	Nanoscale investigation of a radial p-n junction in self-catalyzed GaAs nanowires grown on Si (111). *Nanoscale*, **2018**, 10, 20207-20217	7.7	9
495	Solid-State Nanopore Easy Chip Integration in a Cheap and Reusable Microfluidic Device for Ion Transport and Polymer Conformation Sensing. *ACS Sensors*, **2018**, 3, 2129-2137	9.2	16
494	Atomic Step Flow on a Nanofacet. *Physical Review Letters*, **2018**, 121, 166101	7.4	82
493	A Stress-Free and Textured GaP Template on Silicon for Solar Water Splitting. *Advanced Functional Materials*, **2018**, 28, 1801585	15.6	11
492	Wave-Function Engineering in HgSe/HgTe Colloidal Heterostructures To Enhance Mid-infrared Photoconductive Properties. *Nano Letters*, **2018**, 18, 4590-4597	11.5	19
491	Coupled HgSe Colloidal Quantum Wells through a Tunable Barrier: A Strategy To Uncouple Optical and Transport Band Gap. *Chemistry of Materials*, **2018**, 30, 4065-4072	9.6	23
490	In-plane InSb nanowires grown by selective area molecular beam epitaxy on semi-insulating substrate. *Nanotechnology*, **2018**, 29, 305705	3.4	12
489	Threading dislocation free GaSb nanotemplates grown by selective molecular beam epitaxy on GaAs (001) for in-plane InAs nanowire integration. *Journal of Crystal Growth*, **2017**, 477, 45-49	1.6	9
488	Nanoselective area growth of defect-free thick indium-rich InGaN nanostructures on sacrificial ZnO templates. *Nanotechnology*, **2017**, 28, 195304	3.4	1
487	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. *Journal of Crystal Growth*, **2017**, 477, 65-71	1.6	10

486	Flexible metal-semiconductor-metal device prototype on wafer-scale thick boron nitride layers grown by MOVPE. *Scientific Reports*, **2017**, 7, 786	4.9	35
485	Morphology and valence band offset of GaSb quantum dots grown on GaP(001) and their evolution upon capping. *Nanotechnology*, **2017**, 28, 225601	3.4	6
484	. *IEEE Photonics Journal*, **2017**, 9, 1-7	1.8	14
483	In Situ Optical Monitoring of New Pathways in the Metal-Induced Crystallization of Amorphous Ge. *Crystal Growth and Design*, **2017**, 17, 5783-5789	3.5	5
482	In situ passivation of GaAsP nanowires. *Nanotechnology*, **2017**, 28, 495707	3.4	18
481	Electronic properties of (Sb;Bi)Te colloidal heterostructured nanoplates down to the single particle level. *Scientific Reports*, **2017**, 7, 9647	4.9	4
480	Emission wavelength red-shift by using semi-bulk InGaN buffer layer in InGaN/InGaN multiple-quantum-well. *Superlattices and Microstructures*, **2017**, 112, 279-286	2.8	5
479	Surface effects on exciton diffusion in non polar ZnO/ZnMgO heterostructures. *Journal of Physics Condensed Matter*, **2017**, 29, 485706	1.8	2
478	Functionalized Solid-State Nanopore Integrated in a Reusable Microfluidic Device for a Better Stability and Nanoparticle Detection. *ACS Applied Materials & Interfaces*, **2017**, 9, 41634-41640	9.5	33
477	Gas sensors boosted by two-dimensional h-BN enabled transfer on thin substrate foils: towards wearable and portable applications. *Scientific Reports*, **2017**, 7, 15212	4.9	41
476	Enhanced sputtering of Ge nanowires under synergetic effect of Mn ion and electron beams. *Results in Physics*, **2017**, 7, 3813-3814	3.7	
475	Study of the nucleation and growth of InP nanowires on silicon with gold-indium catalyst. *Journal of Crystal Growth*, **2017**, 458, 96-102	1.6	7
474	Improving InGaN heterojunction solar cells efficiency using a semibulk absorber. *Solar Energy Materials and Solar Cells*, **2017**, 159, 405-411	6.4	17
473	Mask effect in nano-selective- area-growth by MOCVD on thickness enhancement, indium incorporation, and emission of InGaN nanostructures on AlN-buffered Si(111) substrates. *Optical Materials Express*, **2017**, 7, 376	2.6	3
472	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. *Optical Materials Express*, **2017**, 7, 3011	2.6	11
471	Lazarevicite-type short-range ordering in ternary III-V nanowires. *Physical Review B*, **2016**, 94,	3.3	6
470	Selective CO2 methanation on Ru/TiO2 catalysts: unravelling the decisive role of the TiO2 support crystal structure. *Catalysis Science and Technology*, **2016**, 6, 8117-8128	5.5	54
469	Mechanistic Insight and Optimization of InP Nanocrystals Synthesized with Aminophosphines. *Chemistry of Materials*, **2016**, 28, 5925-5934	9.6	74

468	Band Alignment and Minigaps in Monolayer MoS2-Graphene van der Waals Heterostructures. *Nano Letters*, **2016**, 16, 4054-61	11.5	230
467	Sub-nanometrically resolved chemical mappings of quantum-cascade laser active regions. *Semiconductor Science and Technology*, **2016**, 31, 055017	1.8	5
466	Metallic Functionalization of CdSe 2D Nanoplatelets and Its Impact on Electronic Transport. *Journal of Physical Chemistry C*, **2016**, 120, 12351-12361	3.8	26
465	Nondestructive Characterization of Residual Threading Dislocation Density in HgCdTe Layers Grown on CdZnTe by Liquid-Phase Epitaxy. *Journal of Electronic Materials*, **2016**, 45, 4518-4523	1.9	3
464	An ultra-thin SiO2 ALD layer for void-free bonding of III□V material on silicon. *Microelectronic Engineering*, **2016**, 162, 40-44	2.5	4
463	Infrared Photodetection Based on Colloidal Quantum-Dot Films with High Mobility and Optical Absorption up to THz. *Nano Letters*, **2016**, 16, 1282-6	11.5	119
462	Locally measuring the adhesion of InP directly bonded on sub-100 nm patterned Si. *Nanotechnology* , **2016**, 27, 115707	3.4	3
461	Sharpening the Interfaces of Axial Heterostructures in Self-Catalyzed AlGaAs Nanowires: Experiment and Theory. *Nano Letters*, **2016**, 16, 1917-24	11.5	41
460	Chemical lift-off and direct wafer bonding of GaN/InGaN P□N structures grown on ZnO. *Journal of Crystal Growth*, **2016**, 435, 105-109	1.6	2
459	Effect of Dot-Height Truncation on the Device Performance of Multilayer InAs/GaAs Quantum Dot Solar Cells. *IEEE Journal of Photovoltaics*, **2016**, 6, 584-589	3.7	3
458	Photon Cascade from a Single Crystal Phase Nanowire Quantum Dot. *Nano Letters*, **2016**, 16, 1081-5	11.5	28
457	Quantification of the HAADF contrast from the nanometer scale down to the single atomic column: application to quantum cascade lasers **2016**, 572-573		
456	Colloidal Quantum-Dot Heterostructures Studied Using Aberration-Corrected Scanning Transmission Electron Microscopy **2016**, 498-499		
455	Ultrathin PECVD epitaxial Si solar cells on glass via low-temperature transfer process. *Progress in Photovoltaics: Research and Applications*, **2016**, 24, 1075-1084	6.8	24
454	Wet-Route Synthesis and Characterization of Yb:CaF2 Optical Ceramics. *Journal of the American Ceramic Society*, **2016**, 99, 1992-2000	3.8	31
453	Synthesis of In0.1Ga0.9N/GaN structures grown by MOCVD and MBE for high speed optoelectronics. *MRS Advances*, **2016**, 1, 1735-1742	0.7	4
452	Selective area heteroepitaxy of GaSb on GaAs (001) for in-plane InAs nanowire achievement. *Nanotechnology*, **2016**, 27, 505301	3.4	23
451	Nanoparticle Electrical Analysis and Detection with a Solid-state Nanopore in a Microfluidic Device. *Procedia Engineering*, **2016**, 168, 1475-1478		3

450	Probing the electronic properties of CVD graphene superlattices **2016**,		1
449	Nanoselective area growth of GaN by metalorganic vapor phase epitaxy on 4H-SiC using epitaxial graphene as a mask. *Applied Physics Letters*, **2016**, 108, 103105	3.4	9
448	New insights into the Mo/Cu(In,Ga)Se interface in thin film solar cells: Formation and properties of the MoSe interfacial layer. *Journal of Chemical Physics*, **2016**, 145, 154702	3.9	25
447	Role of V-pits in the performance improvement of InGaN solar cells. *Applied Physics Letters*, **2016**, 109, 133507	3.4	6
446	Low temperature plasma enhanced CVD epitaxial growth of silicon on GaAs: a new paradigm for III-V/Si integration. *Scientific Reports*, **2016**, 6, 25674	4.9	16
445	High reflectance dielectric distributed Bragg reflectors for near ultra-violet planar microcavities: SiO2/HfO2 versus SiO2/SiNx. *Journal of Applied Physics*, **2016**, 120, 093107	2.5	3
444	Local probing of the interfacial strength in InP/Si substructures. *MRS Advances*, **2016**, 1, 779-784	0.7	
443	Single-crystal nanopyramidal BGaN by nanoselective area growth on AlN/Si(111) and GaN templates. *Nanotechnology*, **2016**, 27, 115602	3.4	2
442	Pressure-Dependent Photoluminescence Study of Wurtzite InP Nanowires. *Nano Letters*, **2016**, 16, 2926-30	13.5	20
441	Large-Area Two-Dimensional Layered Hexagonal Boron Nitride Grown on Sapphire by Metalorganic Vapor Phase Epitaxy. *Crystal Growth and Design*, **2016**, 16, 3409-3415	3.5	81
440	First orientation-patterned GaSb ridge waveguides fabrication and preliminary characterization for frequency conversion in the mid-infrared **2016**,		1
439	(Invited) Locally Measuring the Adhesion of InP Membranes Directly Bonded on Silicon. *ECS Transactions*, **2016**, 75, 169-176	1	
438	van der Waals Epitaxy of GaSe/Graphene Heterostructure: Electronic and Interfacial Properties. *ACS Nano*, **2016**, 10, 9679-9686	16.7	113
437	Abrupt GaP/GaAs Interfaces in Self-Catalyzed Nanowires. *Nano Letters*, **2015**, 15, 6036-41	11.5	42
436	Quantitative evaluation of microtwins and antiphase defects in GaP/Si nanolayers for a III-V photonics platform on silicon using a laboratory X-ray diffraction setup. *Journal of Applied Crystallography*, **2015**, 48, 702-710	3.8	12
435	Evidence for Flat Bands near the Fermi Level in Epitaxial Rhombohedral Multilayer Graphene. *ACS Nano*, **2015**, 9, 5432-9	16.7	69
434	Nanoscale elemental quantification in heterostructured SiGe nanowires. *Nanoscale*, **2015**, 7, 8544-53	7.7	6
433	Crystallization of Si Templates of Controlled Shape, Size, and Orientation: Toward Micro- and Nanosubstrates. *Crystal Growth and Design*, **2015**, 15, 2102-2109	3.5	3

432	AlGaN-based MQWs grown on a thick relaxed AlGaN buffer on AlN templates emitting at 285 nm. *Optical Materials Express*, **2015**, 5, 380	2.6	26
431	Structural and optical investigations of AlGaN MQWs grown on a relaxed AlGaN buffer on AlN templates for emission at 280 nm. *Journal of Crystal Growth*, **2015**, 432, 37-44	1.6	5
430	Biomimetic Nanotubes Based on Cyclodextrins for Ion-Channel Applications. *Nano Letters*, **2015**, 15, 7748-54	11.5	27
429	Nonstoichiometric Low-Temperature Grown GaAs Nanowires. *Nano Letters*, **2015**, 15, 6440-5	11.5	8
428	Nanostructure and luminescence properties of amorphous and crystalline ytterbium–yttrium oxide thin films obtained with pulsed reactive crossed-beam deposition. *Journal of Materials Science*, **2015**, 50, 1267-1276	4.3	2
427	ZnS anisotropic nanocrystals using a one-pot low temperature synthesis. *New Journal of Chemistry*, **2015**, 39, 90-93	3.6	6
426	Interplay between tightly focused excitation and ballistic propagation of polariton condensates in a ZnO microcavity. *Physical Review B*, **2015**, 92,	3.3	6
425	Nondestructive three-dimensional imaging of crystal strain and rotations in an extended bonded semiconductor heterostructure. *Physical Review B*, **2015**, 92,	3.3	17
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